



SEMITRANS® 4

SKM600GA12V

Features

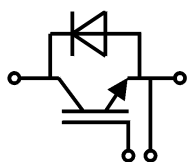
- V-IGBT = 6. Generation Trench V-IGBT (Fuji)
- CAL4 = Soft switching 4. Generation CAL-diode
- Isolated copper baseplate using DBC technology (Direct Copper Bonding)
- UL recognized, file no. E63532
- Increased power cycling capability
- With integrated gate resistor
- Low switching losses at high di/dt

Typical Applications*

- AC inverter drives
- UPS
- Electronic welders
- Switched reluctance motor

Remarks

- Case temperature limited to $T_c = 125^\circ\text{C}$ max, recomm. $T_{op} = -40 \dots +150^\circ\text{C}$, product rel. results valid for $T_j = 150^\circ$



GA

Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
IGBT				
V _{CES}	T _j = 25 °C		1200	V
I _C	T _j = 175 °C	T _c = 25 °C	908	A
		T _c = 80 °C	692	A
I _{Cnom}			600	A
I _{CRM}	I _{CRM} = 3xI _{Cnom}		1800	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 720 V V _{GE} ≤ 15 V V _{CES} ≤ 1200 V	T _j = 125 °C	10	μs
T _j			-40 ... 175	°C
Inverse diode				
I _F	T _j = 175 °C	T _c = 25 °C	707	A
		T _c = 80 °C	529	A
I _{Fnom}			600	A
I _{FRM}	I _{FRM} = 3xI _{Fnom}		1800	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 25 °C		3240	A
T _j			-40 ... 175	°C
Module				
I _{t(RMS)}	T _{terminal} = 80 °C		500	A
T _{stg}			-40 ... 125	°C
V _{isol}	AC sinus 50 Hz, t = 1 min		4000	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
IGBT						
V _{CE(sat)}	I _C = 600 A	T _j = 25 °C		1.75	2.20	V
	V _{GE} = 15 V chipelevel	T _j = 150 °C		2.20	2.50	V
V _{CE0}	chipelevel	T _j = 25 °C		0.94	1.04	V
		T _j = 150 °C		0.88	0.98	V
r _{CE}	V _{GE} = 15 V chipelevel	T _j = 25 °C		1.35	1.93	mΩ
		T _j = 150 °C		2.20	2.53	mΩ
V _{GE(th)}	V _{GE} =V _{CE} , I _C = 24 mA		5.5	6	6.5	V
I _{CES}	V _{GE} = 0 V	T _j = 25 °C		0.1	0.3	mA
	V _{CE} = 1200 V	T _j = 150 °C				mA
C _{ies}	V _{CE} = 25 V V _{GE} = 0 V	f = 1 MHz		36		nF
C _{oes}		f = 1 MHz		3.55		nF
C _{res}		f = 1 MHz		3.536		nF
Q _G	V _{GE} = - 8 V...+ 15 V			6620		nC
R _{Gint}				1.25		Ω
t _{d(on)}	V _{CC} = 600 V	T _j = 150 °C		710		ns
t _r	I _C = 600 A		T _j = 150 °C		85	
E _{on}	V _{GE} = ±15 V	T _j = 150 °C		76		mJ
t _{d(off)}	R _{G on} = 2.5 Ω	T _j = 150 °C		930		ns
t _f	R _{G off} = 2.5 Ω	T _j = 150 °C		98		ns
E _{off}	di/dt _{on} = 9000 A/μs di/dt _{off} = 6000 A/μs du/dt _{off} = 6400 V/μs	T _j = 150 °C		76		mJ
R _{th(j-c)}	per IGBT				0.049	K/W



SEMITRANS® 4

SKM600GA12V

Features

- V-IGBT = 6. Generation Trench V-IGBT (Fuji)
- CAL4 = Soft switching 4. Generation CAL-diode
- Isolated copper baseplate using DBC technology (Direct Copper Bonding)
- UL recognized, file no. E63532
- Increased power cycling capability
- With integrated gate resistor
- Low switching losses at high di/dt

Typical Applications*

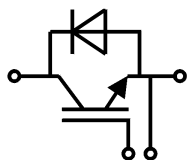
- AC inverter drives
- UPS
- Electronic welders
- Switched reluctance motor

Remarks

- Case temperature limited to $T_c = 125^\circ\text{C}$ max, recomm.
- $T_{op} = -40 \dots +150^\circ\text{C}$, product rel. results valid for $T_j = 150^\circ$

Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
$V_F = V_{EC}$	$I_F = 600\text{ A}$	$T_j = 25^\circ\text{C}$		2.14	2.46	V
	$V_{GE} = 0\text{ V}$	$T_j = 150^\circ\text{C}$		2.07	2.38	V
	chiplevel					
V_{F0}		$T_j = 25^\circ\text{C}$		1.3	1.5	V
	chiplevel	$T_j = 150^\circ\text{C}$		0.9	1.1	V
r_F		$T_j = 25^\circ\text{C}$		1.4	1.6	m Ω
	chiplevel	$T_j = 150^\circ\text{C}$		1.9	2.1	m Ω
I_{RRM}	$I_F = 600\text{ A}$	$T_j = 150^\circ\text{C}$		635		A
Q_{rr}	$di/dt_{off} = 8600\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		118		μC
E_{rr}	$V_{GE} = \pm 15\text{ V}$	$T_j = 150^\circ\text{C}$		43		mJ
	$V_{CC} = 600\text{ V}$					
$R_{th(j-c)}$	per diode				0.086	K/W
Module						
L_{CE}				15	20	nH
$R_{CC'+EE'}$	terminal-chip	$T_c = 25^\circ\text{C}$		0.18		m Ω
		$T_c = 125^\circ\text{C}$		0.22		m Ω
$R_{th(c-s)}$	per module			0.02	0.038	K/W
M_s	to heat sink M6		3		5	Nm
M_t	to terminals	M6	2.5		5	Nm
		M4	1.1		2	Nm
w					330	g



GA

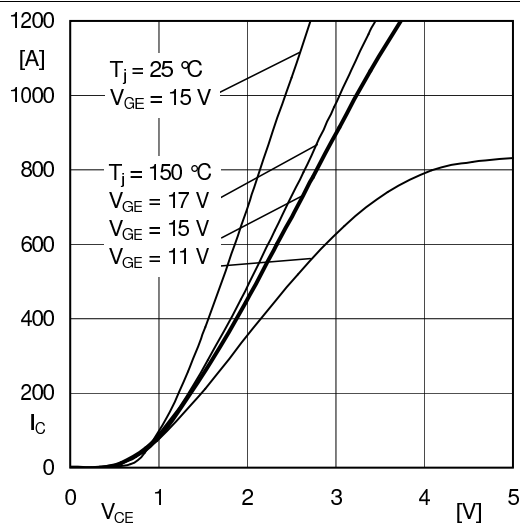


Fig. 1: Typ. output characteristic, inclusive $R_{CC'+EE'}$

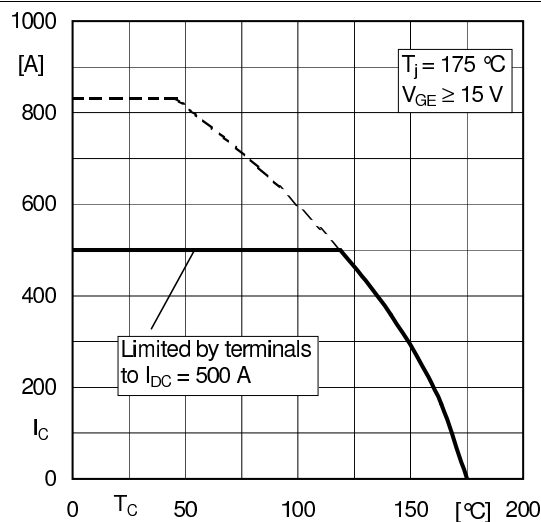


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

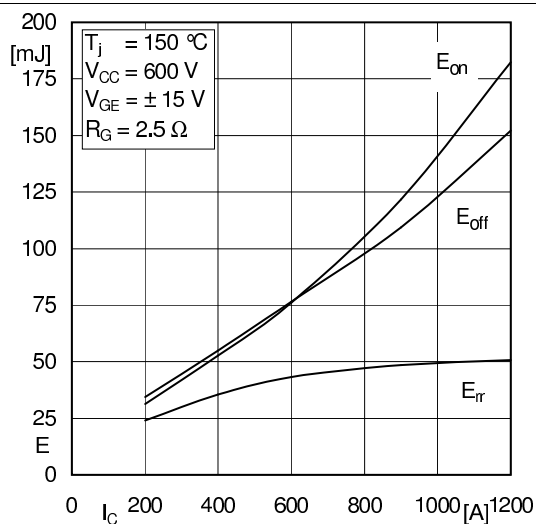


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

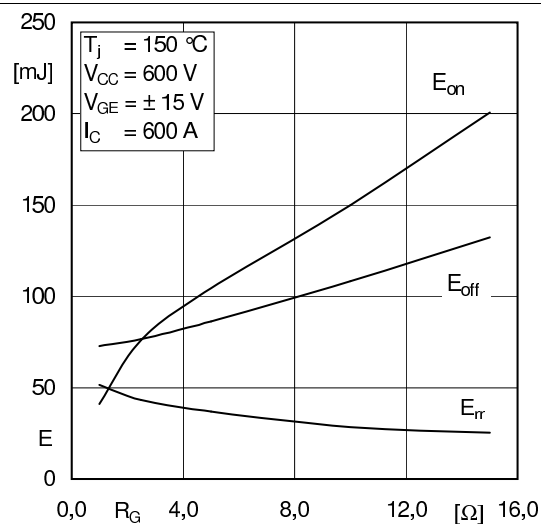


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

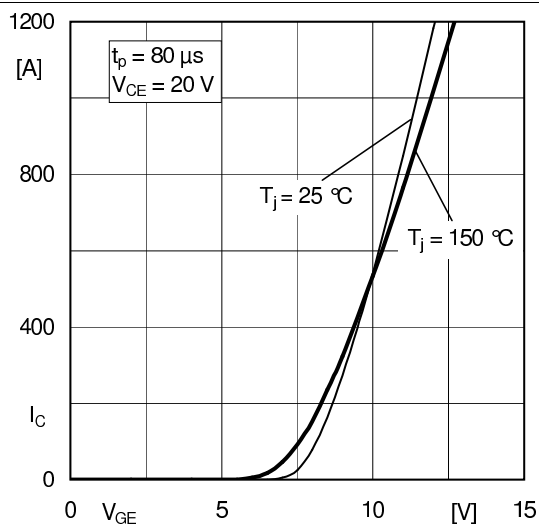


Fig. 5: Typ. transfer characteristic

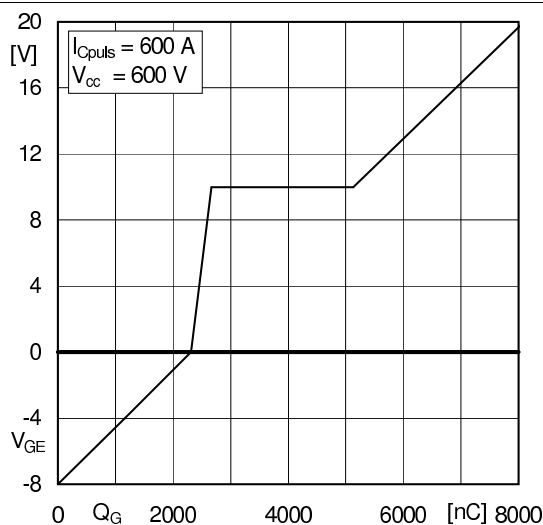
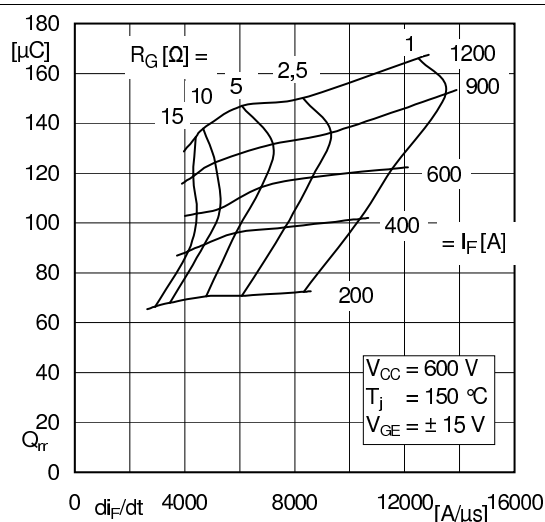
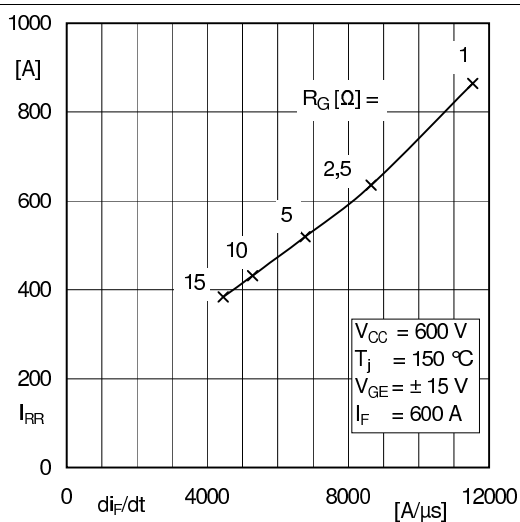
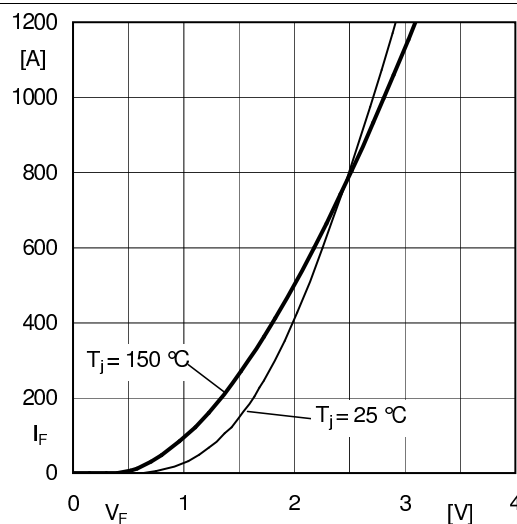
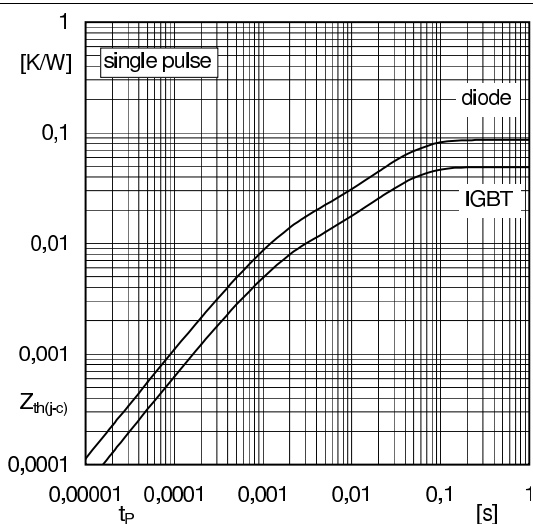
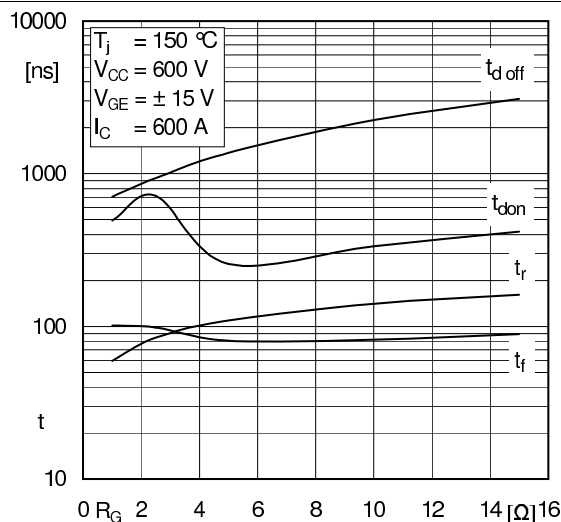
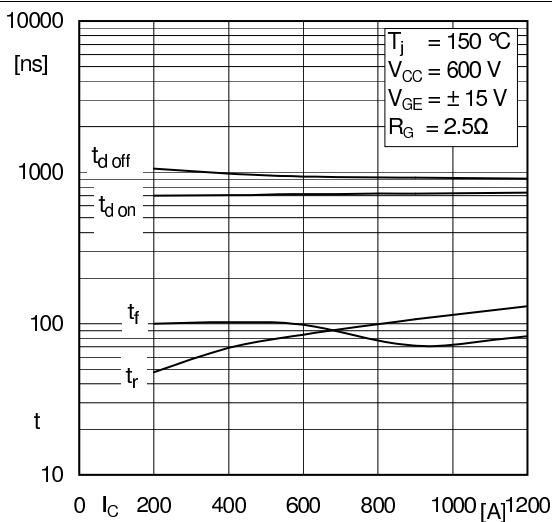
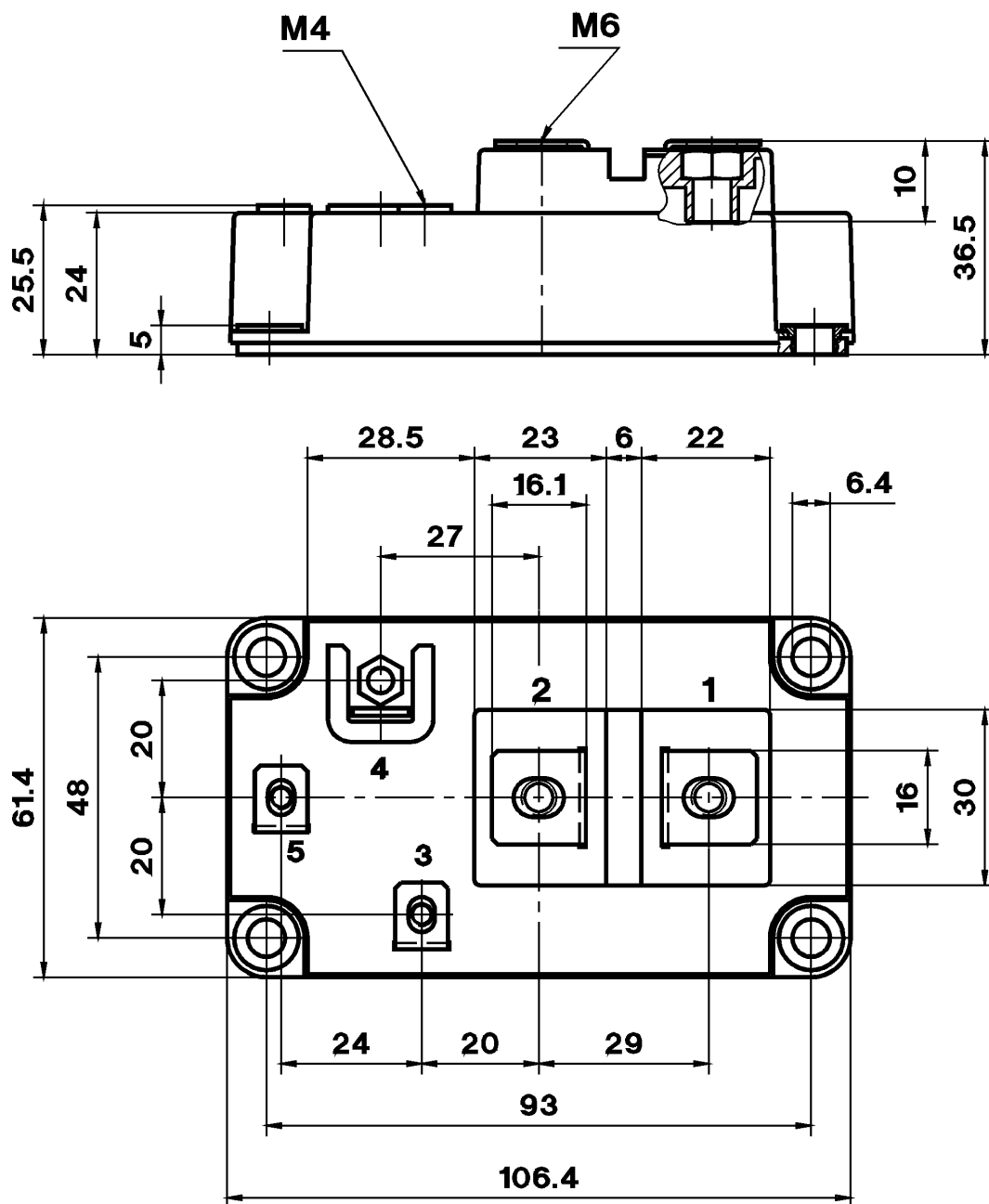
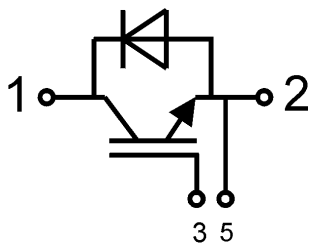


Fig. 6: Typ. gate charge characteristic





SEMITRANS 4



GA

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.